TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (π -MOSVII)

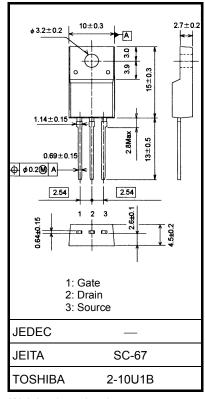
TK4A60DA

Switching Regulator Applications

- Low drain-source ON resistance: $RDS(ON) = 1.7 \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 2.2 \text{ S}$ (typ.)
- Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 600 \ V)$
- Enhancement-mode: $V_{th} = 2.4$ to 4.4 V ($V_{DS} = 10$ V, $I_D = 1$ mA)

Characteristics		Symbol	Rating	Unit		
Drain-source voltage			V _{DSS}	600	V	
Gate-source voltage			V _{GSS}	±30	V	
Drain current	DC (Note	1)	۱ _D	3.5	Α	
	Pulse (Note	1)	I _{DP}	14	A .	
Drain power dissipation (Tc = 25° C)			PD	35	W	
Single pulse avalanche energy (Note 2)			E _{AS}	158	mJ	
Avalanche current			I _{AR}	3.5	А	
Repetitive avalanche energy (Note 3)			E _{AR}	3.5	mJ	
Channel temperature			T _{ch}	150	°C	
Storage temperature range			T _{stg}	-55 to 150	°C	

Absolute Maximum Ratings (Ta = 25°C)



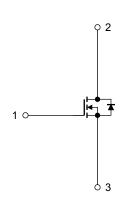
Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	R _{th (ch-c)}	3.57	°C/W
Thermal resistance, channel to ambient	R _{th (ch-a)}	62.5	°C/W

Internal Connection



Start of commercial production 2008-09

Note 1: Please use devices on conditions that the channel temperature is below 150°C.

Note 2: V_{DD} = 90 V, T_{ch} = 25°C (initial), L = 22.5 mH, R_G = 25 Ω , I_{AR} = 3.5 A

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm

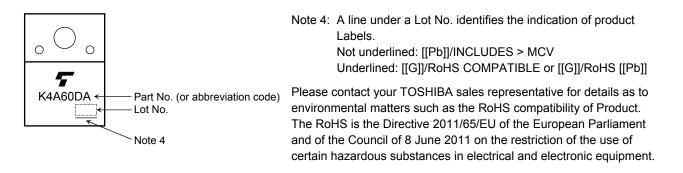
Electrical Characteristics (Ta = 25°C)

Char	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS}=\pm 30~V,~V_{DS}=0~V$	_		±1	μA
Drain cut-off current		I _{DSS}	$V_{DS} = 600 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_	_	10	μA
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	600	_		V
Gate threshold ve	oltage	V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	2.4	_	4.4	V
Drain-source ON	resistance	R _{DS (ON)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 1.8 \text{ A}$	_	1.7	2.2	Ω
Forward transfer	rward transfer admittance $ Y_{fs} $ $V_{DS} = 10 V_{r}$		$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1.8 \text{ A}$	0.6	2.2		S
Input capacitance		C _{iss}		—	490		pF
Reverse transfer capacitance		C _{rss}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz	_	3		
Output capacitance		C _{oss}			55		
Switching time	Rise time	tr	V_{GS} $0 V$ V_{GS} $0 V$ V_{GS} $0 V$ $V_{DD} \approx 200 V$		18		ns
	Turn-on time	t _{on}			40		
	Fall time	t _f			8		
	Turn-off time	t _{off}	Duty \leq 1%, t _w = 10 µs		55		
Total gate charge		Qg		_	11		
Gate-source charge		Q _{gs}	$V_{DD}\approx 400$ V, $V_{GS}=10$ V, $I_{D}=3.5$ A		6		nC
Gate-drain charge		Q _{gd}		_	5		

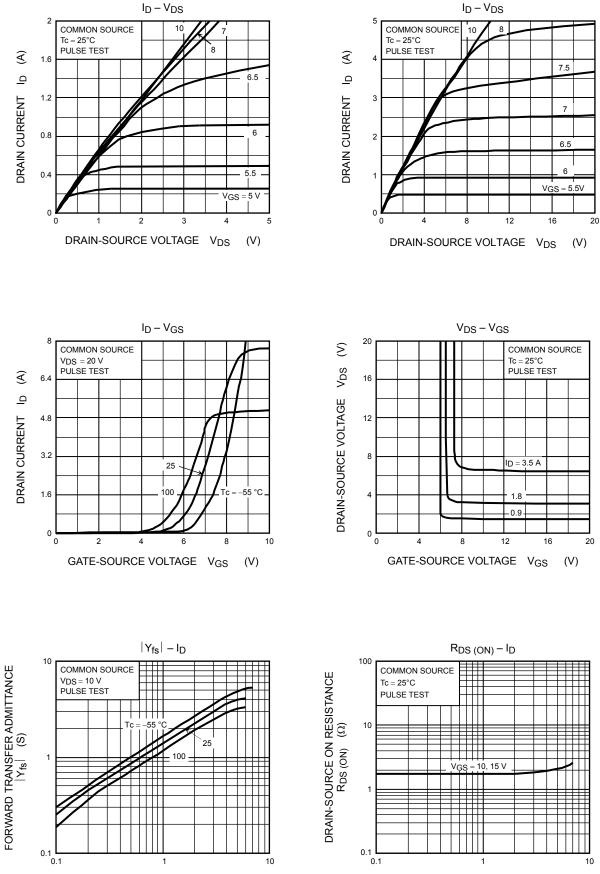
Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	_	_	3.5	А
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	14	А
Forward voltage (diode)	V _{DSF}	I _{DR} = 3.5 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time	t _{rr}	$I_{DR} = 3.5 \text{ A}, V_{GS} = 0 \text{ V},$	_	1000	_	ns
Reverse recovery charge	Q _{rr}	dI _{DR} /dt = 100 A/μs	_	5.0	_	μC

Marking



TOSHIBA



DRAIN CURRENT ID (A)

2013-11-01

DRAIN CURRENT ID (A)

TOSHIBA

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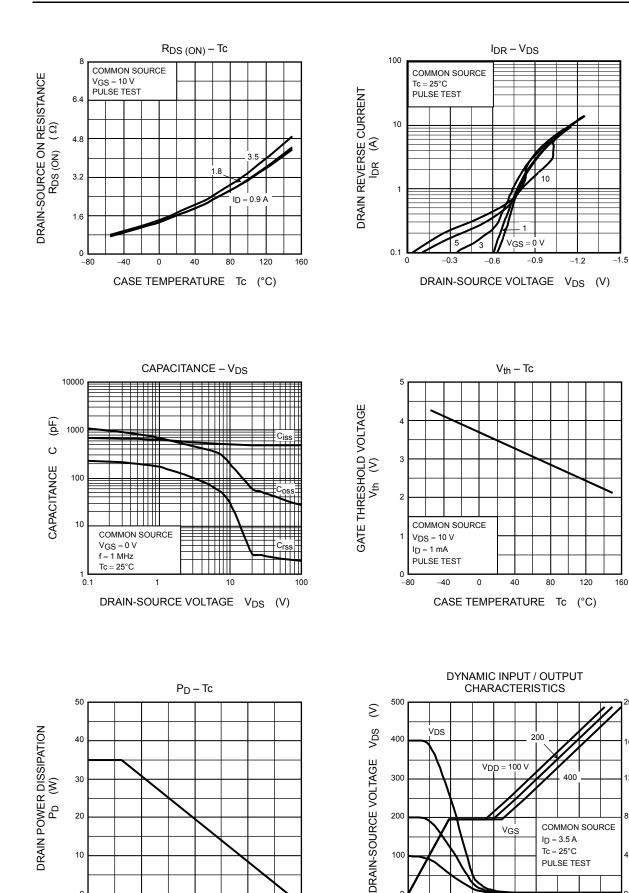
40

80

CASE TEMPERATURE Tc (°C)

120

160



20

16

12

n

20

PULSE TEST

16

(nC)

12

S

Vgs

GATE-SOURCE VOLTAGE

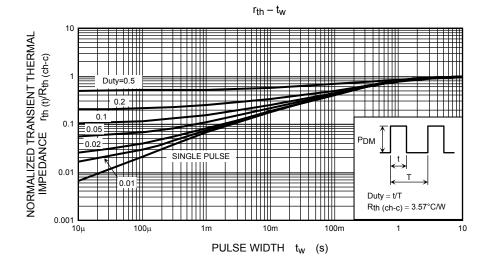
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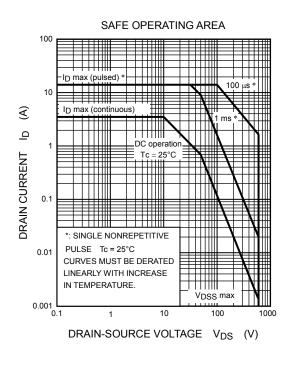
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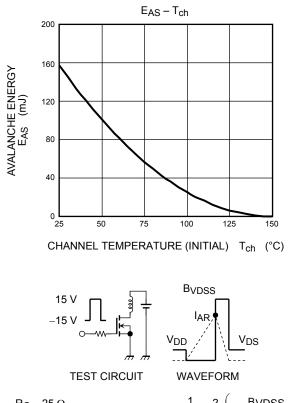
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8

TOTAL GATE CHARGE Qg







 $\begin{array}{l} \mathsf{R}_{G} = 25 \ \Omega \\ \mathsf{V}_{DD} = 90 \ \mathsf{V}, \ \mathsf{L} = 22.5 \ \mathsf{mH} \end{array} \qquad \mathsf{E}_{AS} = \frac{1}{2} \cdot \mathsf{L} \cdot \mathsf{I}^{2} \cdot \left(\frac{\mathsf{B}_{VDSS}}{\mathsf{B}_{VDSS} - \mathsf{V}_{DD}} \right) \\ \end{array}$

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